

10/691 500

**EAST Search History**

| Ref # | Hits | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|---|---|------------------|---------|------------------|
| L1    | 0    | 10/691500   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:40 |
| L2    | 0    | (substrate adj temperature) and semiconductor and estimation and (reaction adj control adj condition) and rate and (optical adj constant) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:43 |
| L3    | 0    | (substrate adj temperature) and semiconductor and estimation and (reaction adj control adj condition)                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:43 |
| L4    | 1    | (substrate adj temperature) and (reaction adj control adj condition)  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:48 |
| L5    | 0    | (temperature adj estimation) and (reaction adj control adj condition) and substrate and semiconductor                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:46 |
| L6    | 0    | temperature and (reaction adj control adj condition) and substrate and semiconductor and (optical adj constant)                           | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:46 |
| L7    | 0    | temperature and (reaction adj control adj condition) and substrate and semiconductor and (single adj crystal adj material)                | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:47 |
| L8    | 0    | temperature and (reaction adj control adj condition) and substrate and semiconductor and (single adj crystal)                             | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/05/02 13:47 |

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| L9  | 324 | (substrate adj temperature) and (single adj crystal adj material) and optical  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:49 |
| L10 | 1   | (substrate adj temperature) and (single adj crystal adj material) and (optical adj constant)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:51 |
| L11 | 1   | "4400577".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:50 |
| L12 | 1   | "4216501".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:50 |
| L13 | 1   | "4166919".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:50 |
| L14 | 1   | "4126150".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:50 |
| L15 | 1   | "4109271".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:51 |
| L16 | 1   | "4064521".PN.  | USPAT;<br>USOCR   | OR | ON | 2006/05/02 13:51 |
| L17 | 1   | 10 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon)        | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:56 |
| L18 | 1   | 11 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:57 |

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| L19 | 1 | 12 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:58 |
| L20 | 1 | 13 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 13:59 |
| L21 | 1 | 14 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:01 |
| L22 | 1 | 15 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:02 |
| L23 | 1 | 16 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:03 |

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| L24 | 1    | 4 and (semiconductor or single or crystal or first or second or third or fourth or surface or reaction or control or condition or optical or constant or temperature or estimation or calculating or measuring or expetial or growing or growth or thickness or substrate or rate or silicon or germanium or carbon or CVD) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:04 |
| L25 | 1086 | 438/660   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:04 |
| L26 | 1562 | 438/680   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:04 |
| L27 | 208  | 438/933   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:04 |
| L28 | 1768 | 438/723   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:04 |
| L29 | 704  | 438/743   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |
| L30 | 179  | 438/752   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |

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|     |      |         |   |    |    |                  |
|-----|------|---------|---|----|----|------------------|
| L31 | 663  | 438/753 | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |
| L32 | 1363 | 438/795 | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |
| L33 | 421  | 438/792 | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |
| L34 | 945  | 438/788 | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/05/02 14:05 |